

Handout 16

Electrical Conduction in Energy Bands

In this lecture you will learn:

- The conductivity of electrons in energy bands
- The electron-hole transformation
- The conductivity tensor
- Examples
- Bloch oscillations

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Inversion Symmetry of Energy Bands

Recall that because of time reversal symmetry:

$$\psi_{n,-\vec{k}}^*(\vec{r}) = \psi_{n,\vec{k}}(\vec{r}) \quad E_n(-\vec{k}) = E_n(\vec{k})$$

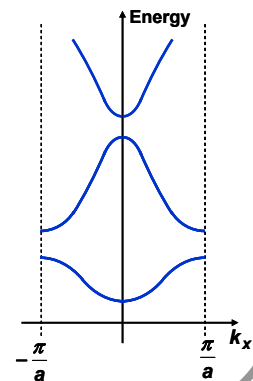
We know that:

$$\vec{v}_n(\vec{k}) = \frac{1}{\hbar} \nabla_{\vec{k}} E_n(\vec{k})$$

Now let \vec{k} go to $-\vec{k}$ in the above equation:

$$\begin{aligned} \vec{v}_n(-\vec{k}) &= \frac{1}{\hbar} \nabla_{-\vec{k}} E_n(-\vec{k}) \\ &= -\frac{1}{\hbar} \nabla_{\vec{k}} E_n(-\vec{k}) \\ &= -\frac{1}{\hbar} \nabla_{\vec{k}} E_n(\vec{k}) \\ &= -\vec{v}_n(\vec{k}) \end{aligned}$$

$$\Rightarrow \vec{v}_n(-\vec{k}) = -\vec{v}_n(\vec{k})$$



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Current Density for Energy Bands

In **Drude model**, the electron current density was given as:

$$\bar{J} = n(-e)\bar{v}$$

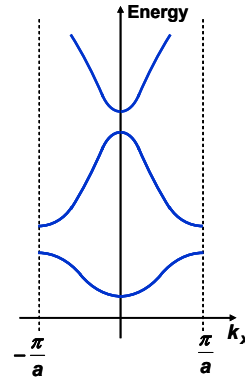
For a **free electron gas** the current density was given as:

$$\bar{J} = (-e)\frac{2}{V} \times \sum_{\text{all } \vec{k}} f(\vec{k})\bar{v}(\vec{k}) = -2e \times \int \frac{d^3\vec{k}}{(2\pi)^3} f(\vec{k})\bar{v}(\vec{k})$$

Now we want to find the current density due to electrons in energy bands

The current density due to electrons in the n -th band can be written in a manner similar to the free-electron case:

$$\begin{aligned} \bar{J}_n &= (-e)\frac{2}{V} \times \sum_{\vec{k} \text{ in FBZ}} f_n(\vec{k})\bar{v}_n(\vec{k}) \\ &= -2e \times \int_{\text{FBZ}} \frac{d^3\vec{k}}{(2\pi)^3} f_n(\vec{k})\bar{v}_n(\vec{k}) \end{aligned}$$



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Current Density for a Completely Filled or Empty Bands

Consider a **completely filled band** for which $f_n(\vec{k}) = 1$ for all \vec{k} in FBZ

Application of an external field will not change anything!

$$\bar{J}_n = -2e \times \int_{\text{FBZ}} \frac{d^3\vec{k}}{(2\pi)^3} f_n(\vec{k})\bar{v}_n(\vec{k}) = -2e \times \int_{\text{FBZ}} \frac{d^3\vec{k}}{(2\pi)^3} \bar{v}_n(\vec{k}) = 0$$

where I have used the fact:

$$\bar{v}_n(-\vec{k}) = -\bar{v}_n(\vec{k})$$

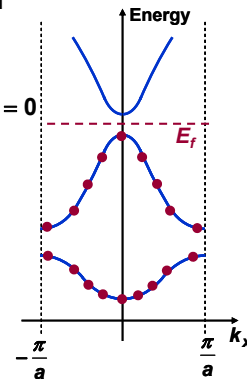
⇒ **Completely filled bands do not contribute to electrical current or to electrical conductivity**

Of course, if $f_n(\vec{k}) = 0$ for all \vec{k} in FBZ:

$$\bar{J}_n = -2e \times \int_{\text{FBZ}} \frac{d^3\vec{k}}{(2\pi)^3} f_n(\vec{k})\bar{v}_n(\vec{k}) = 0$$

⇒ **Completely empty bands do not contribute to electrical current or to electrical conductivity**

Only partially filled bands contribute to electrical current and to electrical conductivity

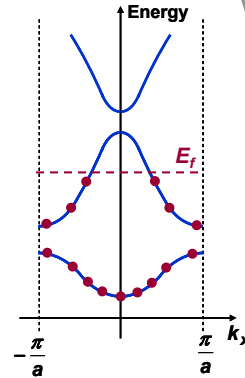


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Current Density and Electron-Hole Transformation

Consider the expression for the current density for a partially filled band:

$$\begin{aligned} \bar{J}_n &= 2(-e) \times \int_{\text{FBZ}} \frac{d^3 \bar{k}}{(2\pi)^3} f_n(\bar{k}) \bar{v}_n(\bar{k}) \longrightarrow (1) \\ &= 2(e) \times \int_{\text{FBZ}} \frac{d^3 \bar{k}}{(2\pi)^3} [1 - f_n(\bar{k}) - 1] \bar{v}_n(\bar{k}) \\ &= \cancel{-2e} \times \int_{\text{FBZ}} \frac{d^3 \bar{k}}{(2\pi)^3} \bar{v}_n(\bar{k}) + 2e \times \int_{\text{FBZ}} \frac{d^3 \bar{k}}{(2\pi)^3} [1 - f_n(\bar{k})] \bar{v}_n(\bar{k}) \\ &= 2(+e) \times \int_{\text{FBZ}} \frac{d^3 \bar{k}}{(2\pi)^3} [1 - f_n(\bar{k})] \bar{v}_n(\bar{k}) \longrightarrow (2) \end{aligned}$$



The final result implies that since the current density of a filled band is zero, the current density for any band can always be expressed in two equivalent ways:

- As an integral over all the **occupied states** assuming **negatively charged particles** (as in (1) above)
- As an integral over all the **unoccupied states** assuming **positively charged particles** (as in (2) above)

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Current Density and Electron-Hole Transformation

One has two choices when calculating current from a partially filled band:

The Electron Choice:

The current density is given by:

$$\bar{J}_n = 2(-e) \times \int_{\text{FBZ}} \frac{d^3 \bar{k}}{(2\pi)^3} f_n(\bar{k}) \bar{v}_n(\bar{k})$$

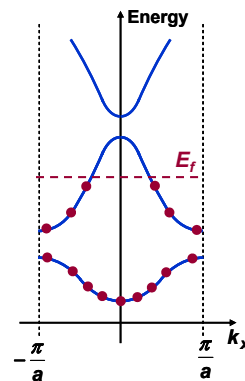
- Current is understood to be due to negatively charged electrons
- This choice is better when the electron number is smaller than the hole number

The Hole Choice:

The current density is given by:

$$\bar{J}_n = 2(+e) \times \int_{\text{FBZ}} \frac{d^3 \bar{k}}{(2\pi)^3} [1 - f_n(\bar{k})] \bar{v}_n(\bar{k})$$

- Current is understood to be due to positively charged fictitious particles called “holes”
- This choice is better when the hole number is smaller than the electron number



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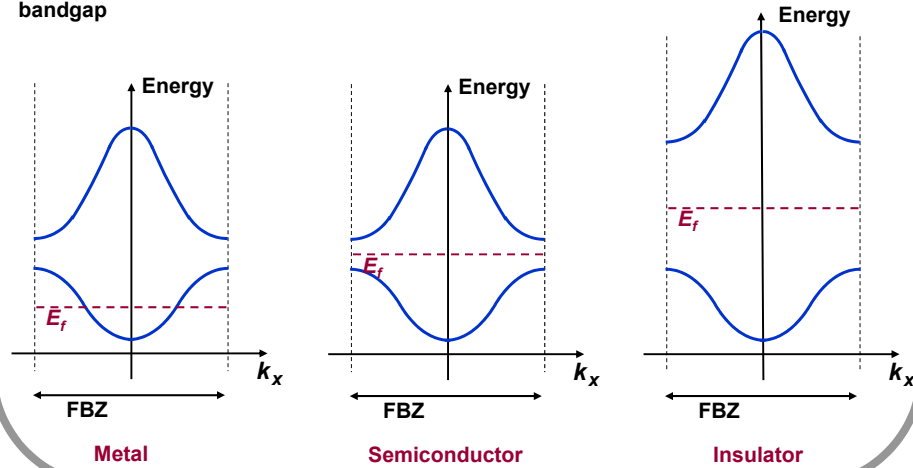
Metals, Semiconductors, and Insulators

Materials can be classified into three main categories w.r.t. their electrical properties:

Metals: In metals, the highest filled band is partially filled (usually half-filled)

Semiconductors: In semiconductors, the highest filled band is completely filled (at least at zero temperature)

Insulators: Insulators are like semiconductors but usually have a much larger bandgap



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Inclusion of Scattering in the Dynamical Equation

In the presence of a uniform electric field the crystal momentum satisfies the dynamical equation:

$$\frac{d \hbar \vec{k}(t)}{dt} = -e \vec{E}$$

Now we need to add the effect of electron scattering.

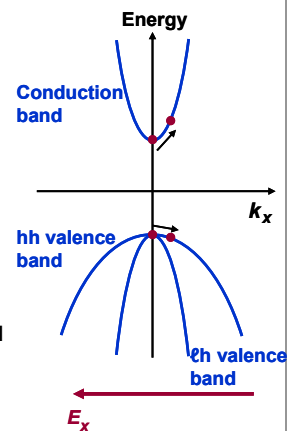
As in the free-electron case, we assume that scattering adds damping:

$$\frac{d \hbar \vec{k}(t)}{dt} = -e \vec{E} - \frac{\hbar [\vec{k}(t) - \vec{k}]}{\tau}$$

The boundary condition is that: $\vec{k}(t=0) = \vec{k}$

Note: the damping term ensures that when the field is turned off, the crystal momentum of the electron goes back to its original value

Steady State Solution: $\vec{k}(t = \infty) = \vec{k} - \frac{e \tau}{\hbar} \vec{E}$



In the presence of an electric field, the crystal momentum of every electron is shifted by an equal amount that is determined by the scattering time and the field strength

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Electrical Conductivity: Conduction Band

Consider a solid in which the energy dispersion for conduction band near a band minimum is given by:

$$E_c(\vec{k}) = E_c(\vec{k}_0) + \frac{\hbar^2}{2} (\vec{k} - \vec{k}_0)^T \cdot M^{-1} \cdot (\vec{k} - \vec{k}_0)$$

The velocity of electrons is:

$$\vec{v}_c(\vec{k}) = M^{-1} \cdot \hbar (\vec{k} - \vec{k}_0)$$

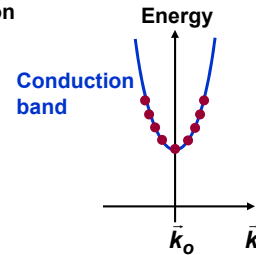
The current density is:

$$\vec{J}_c = -2 e \times \int_{\text{near } \vec{k}_0} \frac{d^3 \vec{k}}{(2\pi)^3} f_c(\vec{k}) \vec{v}_c(\vec{k})$$

In **equilibrium**, for every state with crystal momentum $(\vec{k} - \vec{k}_0)$ that is occupied, the state $-(\vec{k} - \vec{k}_0)$ is also occupied and these two states have opposite velocities.

Therefore in **equilibrium**:

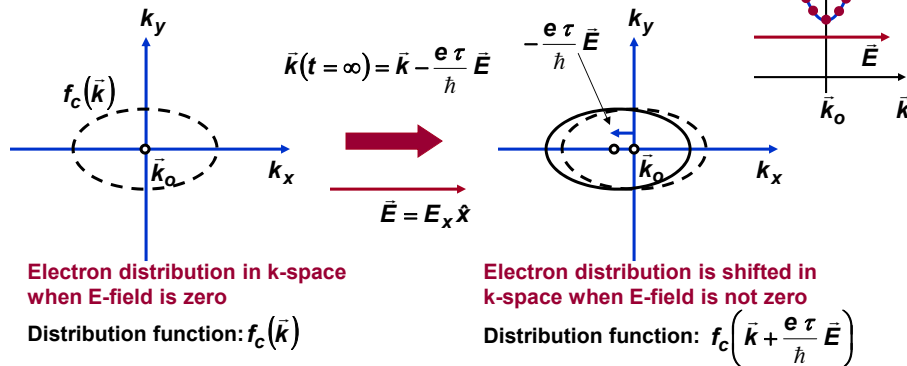
$$\vec{J}_c = -2 e \times \int_{\text{near } \vec{k}_0} \frac{d^3 \vec{k}}{(2\pi)^3} f_c(\vec{k}) \vec{v}_c(\vec{k}) = 0$$



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Electrical Conductivity: Conduction Band

Now assume that an electric field is present that shifts the crystal momentum of all electrons:



Electron distribution in k-space when E-field is zero

Distribution function: $f_c(\vec{k})$

Electron distribution is shifted in k-space when E-field is not zero

Distribution function: $f_c\left(\vec{k} + \frac{e \tau}{\hbar} \vec{E}\right)$

Since the wavevector of each electron is shifted by the same amount in the presence of the E-field, the net effect in k-space is that the entire electron distribution is shifted as shown

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Electrical Conductivity: Conduction Band

Current Density:

$$\bar{J}_c = -2 e \times \int_{\text{near } \bar{k}_0} \frac{d^3 \bar{k}}{(2\pi)^3} f_c \left(\bar{k} + \frac{e\tau}{\hbar} \bar{E} \right) \bar{v}_c(\bar{k})$$

Do a shift in the integration variable:

$$\bar{J}_c = -2 e \times \int_{\text{near } \bar{k}_0} \frac{d^3 \bar{k}}{(2\pi)^3} f_c(\bar{k}) \bar{v}_c \left(\bar{k} - \frac{e\tau}{\hbar} \bar{E} \right)$$

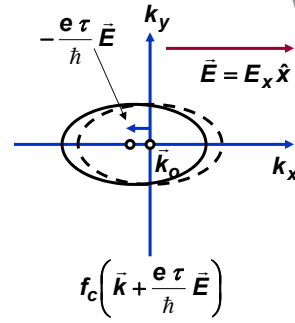
$$\bar{J}_c = -2 e \times \int_{\text{near } \bar{k}_0} \frac{d^3 \bar{k}}{(2\pi)^3} f_c(\bar{k}) M^{-1} \cdot \hbar \left(\bar{k} - \bar{k}_0 - \frac{e\tau}{\hbar} \bar{E} \right)$$

$$\bar{J}_c = e^2 \tau \left[2 \times \int_{\text{near } \bar{k}_0} \frac{d^3 \bar{k}}{(2\pi)^3} f_c(\bar{k}) \right] M^{-1} \cdot \bar{E}$$

$$\bar{J}_c = n e^2 \tau M^{-1} \cdot \bar{E}$$

$$= \bar{\sigma} \cdot \bar{E}$$

Where the conductivity is now a tensor given by: $\bar{\sigma} = n e^2 \tau M^{-1}$



Electrical Conductivity Example: Conduction Band of GaAs

Consider the conduction band of GaAs near the Γ -point:

$$M^{-1} = \begin{bmatrix} 1/m_e & 0 & 0 \\ 0 & 1/m_e & 0 \\ 0 & 0 & 1/m_e \end{bmatrix} \quad \text{Isotropic!}$$

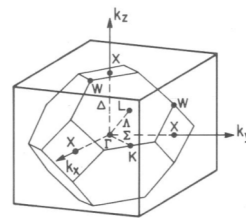
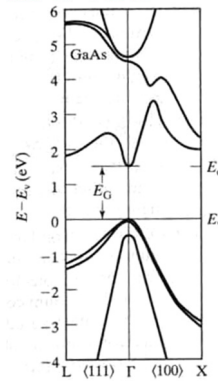
This implies:

$$\bar{J}_c = n e^2 \tau M^{-1} \cdot \bar{E}$$

$$\begin{bmatrix} J_{x,c} \\ J_{y,c} \\ J_{z,c} \end{bmatrix} = n e^2 \tau \begin{bmatrix} 1/m_e & 0 & 0 \\ 0 & 1/m_e & 0 \\ 0 & 0 & 1/m_e \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix}$$

$$= \frac{n e^2 \tau}{m_e} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix} = \sigma \bar{E}$$

$$\Rightarrow \sigma = \frac{n e^2 \tau}{m_e}$$



Electrical Conductivity Example: Conduction Band of Silicon

In Silicon there are six conduction band minima (valleys) that occur along the six Γ -X directions. For the one that occurs along the Γ -X($2\pi/a, 0, 0$) direction:

$$\vec{k}_0 = 0.85 \left(\frac{2\pi}{a}, 0, 0 \right)$$

$$M^{-1} = \begin{bmatrix} 1/m_\ell & 0 & 0 \\ 0 & 1/m_t & 0 \\ 0 & 0 & 1/m_t \end{bmatrix}$$

Not isotropic!

$$m_\ell = 0.92 m$$

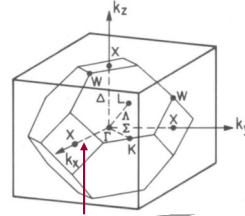
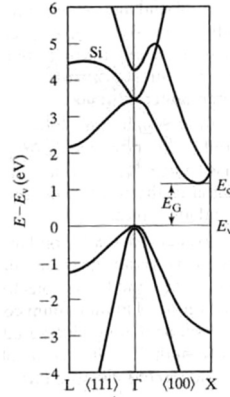
$$m_t = 0.19 m$$

This implies that for this valley:

$$\vec{J}_c = \frac{n}{6} e^2 \tau M^{-1} \cdot \vec{E}$$

$$\begin{bmatrix} J_{x,c} \\ J_{y,c} \\ J_{z,c} \end{bmatrix} = \frac{n}{6} e^2 \tau \begin{bmatrix} 1/m_\ell & 0 & 0 \\ 0 & 1/m_t & 0 \\ 0 & 0 & 1/m_t \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix}$$

The factor of 6 is there because only 1/6th of the total conduction electron density in Silicon is in one valley



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Electrical Conductivity Example: Conduction Band of Silicon

To find the conductivity tensor for Silicon one needs to sum over the current density contributions from all six valleys:

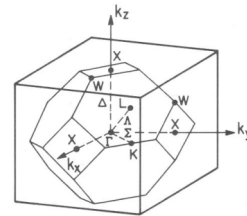
$$\begin{bmatrix} J_{x,c} \\ J_{y,c} \\ J_{z,c} \end{bmatrix} = \frac{n}{6} e^2 \tau \begin{bmatrix} 2/m_\ell + 4/m_t & 0 & 0 \\ 0 & 2/m_\ell + 4/m_t & 0 \\ 0 & 0 & 2/m_\ell + 4/m_t \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix}$$

Isotropic!

$$= \frac{n e^2 \tau}{m_e} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix} = \sigma \vec{E}$$

$$\frac{1}{m_e} = \frac{1}{3} \left(\frac{1}{m_\ell} + \frac{2}{m_t} \right) = \text{Conductivity effective mass}$$

After adding the current density contributions from all six valleys, the resulting conductivity tensor in Silicon is isotropic and described by a conductivity effective mass



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Electrical Conductivity: Valence Band

Consider a solid in which the energy dispersion for valence band near a band maximum is given by:

$$E_v(\vec{k}) = E_v(\vec{k}_0) + \frac{\hbar^2}{2} (\vec{k} - \vec{k}_0)^T \cdot M^{-1} \cdot (\vec{k} - \vec{k}_0)$$

The velocity of electrons is:

$$\vec{v}_v(\vec{k}) = M^{-1} \cdot \hbar (\vec{k} - \vec{k}_0)$$

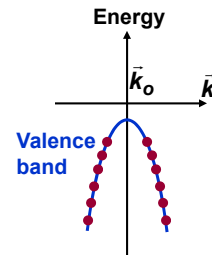
The current density is (using the electron-hole transformation):

$$\vec{J}_v = -2 e \times \int_{\text{near } \vec{k}_0} \frac{d^3 \vec{k}}{(2\pi)^3} f_v(\vec{k}) \vec{v}_v(\vec{k}) = 2 e \times \int_{\text{near } \vec{k}_0} \frac{d^3 \vec{k}}{(2\pi)^3} [1 - f_v(\vec{k})] \vec{v}_v(\vec{k})$$

In **equilibrium**, for every state with crystal momentum $(\vec{k} - \vec{k}_0)$ that is unoccupied, the state $-(\vec{k} - \vec{k}_0)$ is also unoccupied and these two states have opposite velocities.

Therefore in **equilibrium**:

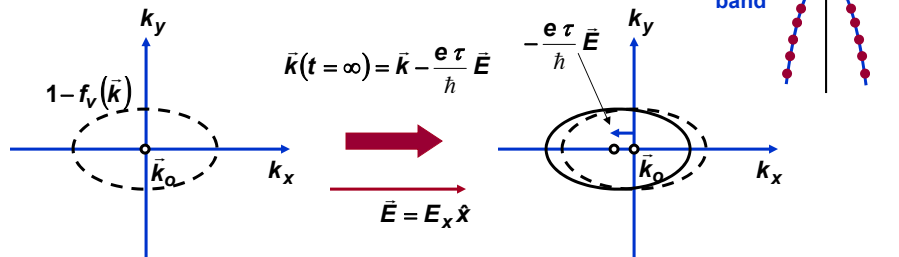
$$\vec{J}_v = 2 e \times \int_{\text{near } \vec{k}_0} \frac{d^3 \vec{k}}{(2\pi)^3} [1 - f_v(\vec{k})] \vec{v}_v(\vec{k}) = 0$$



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Electrical Conductivity: Valence Band

Now assume that an electric field is present that shifts the crystal momentum of all electrons in the valence band:



Hole distribution in k-space when E-field is zero

Distribution function: $1 - f_v(\vec{k})$

Hole distribution is shifted in k-space when E-field is not zero

Distribution function: $1 - f_v\left(\vec{k} + \frac{e \tau}{\hbar} \vec{E}\right)$

Since the wavevector of each electron is shifted by the same amount in the presence of the E-field, the net effect in k-space is that the entire electron distribution (and hole distribution) is shifted as shown

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Electrical Conductivity: Valence Band

Current Density:

$$\bar{J}_V = 2 e \times \int_{\text{near } \bar{k}_0} \frac{d^3 \bar{k}}{(2\pi)^3} \left[1 - f_V \left(\bar{k} + \frac{e\tau}{\hbar} \bar{E} \right) \right] \bar{v}_V(\bar{k})$$

Do a shift in the integration variable:

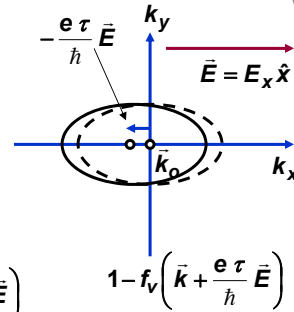
$$\bar{J}_V = 2 e \times \int_{\text{near } \bar{k}_0} \frac{d^3 \bar{k}}{(2\pi)^3} \left[1 - f_V(\bar{k}) \right] \bar{v}_V \left(\bar{k} - \frac{e\tau}{\hbar} \bar{E} \right)$$

$$\bar{J}_V = 2 e \times \int_{\text{near } \bar{k}_0} \frac{d^3 \bar{k}}{(2\pi)^3} \left[1 - f_V(\bar{k}) \right] M^{-1} \cdot \hbar \left(\bar{k} - \bar{k}_0 - \frac{e\tau}{\hbar} \bar{E} \right)$$

$$\bar{J}_V = -e^2 \tau \left[2 \times \int_{\text{near } \bar{k}_0} \frac{d^3 \bar{k}}{(2\pi)^3} \left[1 - f_V(\bar{k}) \right] M^{-1} \cdot \bar{E} \right]$$

$$\bar{J}_V = -\rho e^2 \tau M^{-1} \cdot \bar{E} \\ = \bar{\sigma} \cdot \bar{E}$$

Where the conductivity is now a tensor given by: $\bar{\sigma} = -\rho e^2 \tau M^{-1}$



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Electrical Conductivity Example: Heavy-Hole Band of GaAs

Consider the heavy-hole band of GaAs near the Γ -point:

$$M^{-1} = \begin{bmatrix} -1/m_{hh} & 0 & 0 \\ 0 & -1/m_{hh} & 0 \\ 0 & 0 & -1/m_{hh} \end{bmatrix} \quad \text{Isotropic!}$$

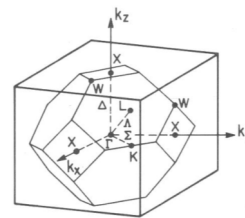
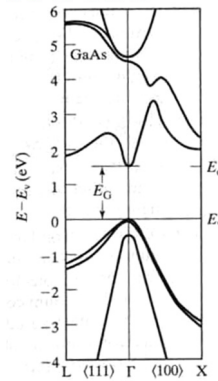
This implies:

$$\bar{J}_{hh} = -\rho_{hh} e^2 \tau M^{-1} \cdot \bar{E}$$

$$\begin{bmatrix} J_{x, hh} \\ J_{y, hh} \\ J_{z, hh} \end{bmatrix} = -\rho_{hh} e^2 \tau \begin{bmatrix} -1/m_{hh} & 0 & 0 \\ 0 & -1/m_{hh} & 0 \\ 0 & 0 & -1/m_{hh} \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix}$$

$$= \frac{\rho_{hh} e^2 \tau}{m_{hh}} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix} = \sigma \bar{E}$$

$$\Rightarrow \sigma = \frac{\rho_{hh} e^2 \tau}{m_{hh}}$$



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Electrical Conductivity Example: Light-Hole Band of GaAs

Consider the light-hole band of GaAs near the Γ -point:

$$M^{-1} = \begin{bmatrix} -1/m_{\ell h} & 0 & 0 \\ 0 & -1/m_{\ell h} & 0 \\ 0 & 0 & -1/m_{\ell h} \end{bmatrix} \quad \text{Isotropic!}$$

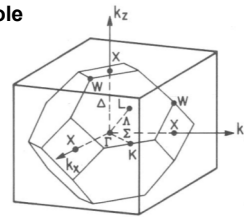
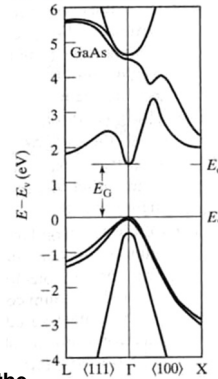
This implies:

$$\bar{J}_{\ell h} = -p_{\ell h} e^2 \tau M^{-1} \cdot \bar{E} = \sigma \bar{E}$$

$$\Rightarrow \sigma = \frac{p_{\ell h} e^2 \tau}{m_{\ell h}}$$

The total valence band conductivity of GaAs can be written as the sum of the contributions from the heavy-hole and the light-hole bands:

$$\sigma = \frac{p_{hh} e^2 \tau}{m_{hh}} + \frac{p_{\ell h} e^2 \tau}{m_{\ell h}}$$



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The Phenomenology Of Transport

The presence of external fields, and scattering, the following relations work for electrons in any energy band near the band edge (assuming parabolic bands):

$$\frac{d \hbar \bar{k}(t)}{dt} = -e \bar{E} - \frac{\hbar [\bar{k}(t) - \bar{k}]}{\tau}$$

$$\bar{v}_n(\bar{k}(t)) = M^{-1} \cdot \hbar (\bar{k}(t) - \bar{k}_0)$$

$$\bar{J}_n(t) = -2 e \times \int_{\text{FBZ}} \frac{d^3 \bar{k}}{(2\pi)^3} f_n(\bar{k}) \bar{v}_n(\bar{k}(t)) = +2 e \times \int_{\text{FBZ}} \frac{d^3 \bar{k}}{(2\pi)^3} [1 - f_n(\bar{k})] \bar{v}_n(\bar{k}(t))$$

The first two can also be written as:

$$M \cdot \frac{d [\bar{v}_n(\bar{k}(t)) - \bar{v}_n(\bar{k})]}{dt} = -e \bar{E} - \frac{M \cdot [\bar{v}_n(\bar{k}(t)) - \bar{v}_n(\bar{k})]}{\tau}$$

Problem: One needs simple models for current transport so that non-specialists, like circuit designers, can understand devices and circuits without having to understand energy bands

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Drift Velocity and Mobility for Electrons

We define the **drift velocity** for the electrons in the conduction band (for parabolic bands) as:

$$\bar{v}_e(t) = \bar{v}_c(\bar{k}(t)) - \bar{v}_c(\bar{k})$$

The **drift velocity is independent of wavevector for parabolic bands** and satisfies:

$$M \cdot \frac{d\bar{v}_e(t)}{dt} = -e \bar{E} - \frac{M \cdot \bar{v}_e(t)}{\tau} \longrightarrow (1)$$

In steady state:

$$\bar{v}_e(t \rightarrow \infty) = \bar{v}_c(\bar{k}(t \rightarrow \infty)) - \bar{v}_c(\bar{k}) = -e\tau M^{-1} \cdot \bar{E} = -\bar{\mu}_e \cdot \bar{E} \quad \left\{ \begin{array}{l} \bar{\mu}_e = \text{mobility tensor} \end{array} \right.$$

Once the drift velocity is calculated, the electron current density is:

$$\begin{aligned} \bar{J}_e(t) &= -2e \times \int_{\text{FBZ}} \frac{d^3\bar{k}}{(2\pi)^3} f_c(\bar{k}) \bar{v}_c(\bar{k}(t)) = -2e \times \int_{\text{FBZ}} \frac{d^3\bar{k}}{(2\pi)^3} f_c(\bar{k}) [\bar{v}_c(\bar{k}(t)) - \bar{v}_c(\bar{k}) + \bar{v}_c(\bar{k})] \\ &= -2e \times \int_{\text{FBZ}} \frac{d^3\bar{k}}{(2\pi)^3} f_c(\bar{k}) [\bar{v}_e(t)] = n(-e)v_e(t) \longrightarrow (2) \end{aligned}$$

Electrons in the conduction band are to be thought of as **negatively charged particles**. In case of multiple electron pockets, current density contributions are calculated separately for each and added in the end.

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Drift Velocity and Mobility for Holes

We define the **drift velocity** for the “holes” in the valence band (assuming parabolic bands) as:

$$\bar{v}_h(t) = \bar{v}_v(\bar{k}(t)) - \bar{v}_v(\bar{k})$$

The **drift velocity is independent of wavevector** and satisfies the equation:

$$(-M) \cdot \frac{d\bar{v}_h(t)}{dt} = +e \bar{E} - \frac{(-M) \cdot \bar{v}_h(t)}{\tau} \longrightarrow (1)$$

Where realizing that the inverse effective mass tensor will have negative diagonal terms for valence band, I have multiplied throughout by a negative sign, with the result that the charge “-e” becomes “+e”

$$\text{In steady state: } \bar{v}_h(t \rightarrow \infty) = -e\tau M^{-1} \cdot \bar{E} = \bar{\mu}_h \cdot \bar{E} \quad \left\{ \begin{array}{l} \bar{\mu}_h = \text{mobility tensor} \end{array} \right.$$

Once the drift velocity is calculated, the hole current density is:

$$\bar{J}_h(t) = +2e \times \int_{\text{FBZ}} \frac{d^3\bar{k}}{(2\pi)^3} [1 - f_v(\bar{k})] \bar{v}_v(\bar{k}(t)) = p(+e)v_h(t) \longrightarrow (2)$$

Holes in the valence band are to be thought of as **positively charged particles**. In case of degenerate valence band maxima, the heavy and light hole current density contributions are calculated separately and added in the end.

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The Case of No Scattering: Bloch Oscillations

Consider an electron in a 1D crystal subjected to a uniform electric field. The energy band dispersion and velocity are:

$$E_n(k_x) = E_s - 2 V_{ss\sigma} \cos(k_x a)$$

$$v_n(k_x) = \frac{1}{\hbar} \frac{dE_n(k_x)}{dk_x} = 2a V_{ss\sigma} \sin(k_x a)$$

In the absence of scattering, the crystal momentum satisfies the dynamical equation:

$$\frac{d \hbar k_x(t)}{dt} = e E_o$$

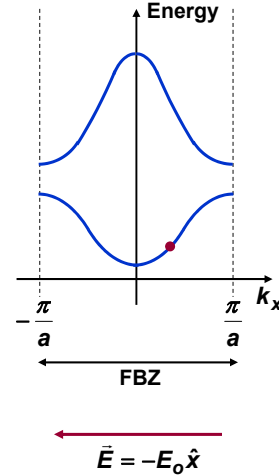
$$\Rightarrow k_x(t) = \frac{e E_o}{\hbar} t + k_x(t=0)$$

The time-dependent velocity of the electron is:

$$v_n(t) = 2a V_{ss\sigma} \sin(k_x(t)a)$$

$$= 2a V_{ss\sigma} \sin\left(\frac{e a E_o}{\hbar} t + k_x(t=0)a\right)$$

Periodic!



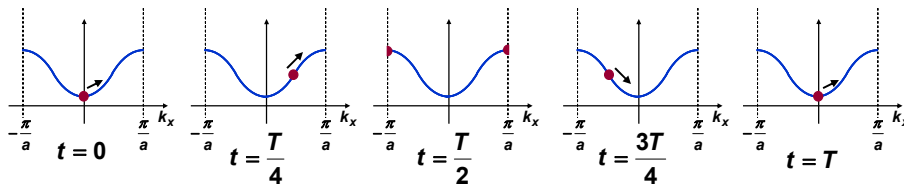
The Case of No Scattering: Bloch Oscillations

A periodic velocity means that the electron motion in real space is also periodic:

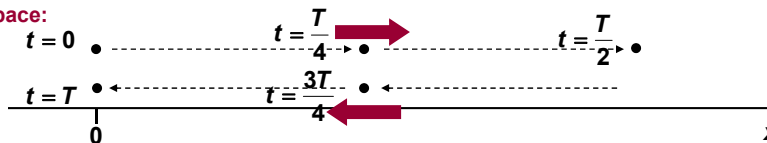
$$\frac{dx(t)}{dt} = v_n(t) = 2a V_{ss\sigma} \sin\left(\frac{e a E_o}{\hbar} t + k_x(t=0)a\right)$$

$$\Rightarrow \int_0^T \frac{dx(t)}{dt} dt = x(t=T) - x(t=0) = 0 \quad \text{where the period } T \text{ is: } T = \frac{2\pi \hbar}{e a E_o}$$

Reciprocal space:



Real space:



Conductivity of Electrons in Graphene

$$\vec{k}_0 = K$$

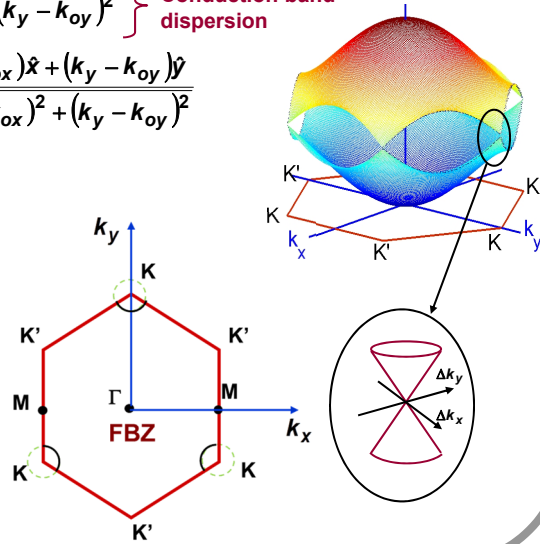
$$E_c(\vec{k}) \approx E_p + \hbar v \sqrt{(k_x - k_{ox})^2 + (k_y - k_{oy})^2} \quad \left. \vphantom{E_c(\vec{k})} \right\} \text{Conduction band dispersion}$$

$$\begin{aligned} \vec{v}_c(\vec{k}) &= \frac{1}{\hbar} \nabla_{\vec{k}} E_c(\vec{k}) = v \frac{(k_x - k_{ox})\hat{x} + (k_y - k_{oy})\hat{y}}{\sqrt{(k_x - k_{ox})^2 + (k_y - k_{oy})^2}} \\ &= v \frac{\vec{k} - \vec{k}_0}{|\vec{k} - \vec{k}_0|} = v \frac{\Delta\vec{k}}{|\Delta\vec{k}|} \end{aligned}$$

The dynamical equation for the crystal momentum still works:

$$\frac{d \hbar \vec{k}(t)}{dt} = -e \vec{E} - \frac{\hbar [\dot{\vec{k}}(t) - \vec{k}]}{\tau}$$

$$\Rightarrow \vec{k}(t = \infty) = \vec{k} - \frac{e \tau}{\hbar} \vec{E}$$

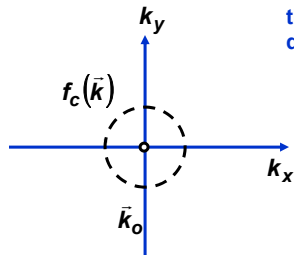


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Conductivity of Electrons in Graphene

$$\vec{k}(t = \infty) = \vec{k} - \frac{e \tau}{\hbar} \vec{E} \quad \rightarrow \quad \vec{v}_c(\vec{k}(t)) = v \frac{\vec{k} - e\tau\vec{E}/\hbar - \vec{k}_0}{|\vec{k} - e\tau\vec{E}/\hbar - \vec{k}_0|}$$

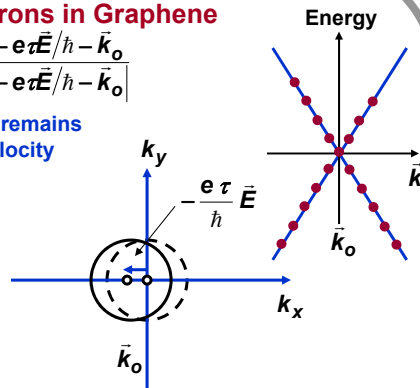
Velocity magnitude remains the same but the velocity direction changes



Electron distribution in k-space when E-field is zero

Distribution function: $f_c(\vec{k})$

$$\vec{E} = E_x \hat{x}$$



Electron distribution is shifted in k-space when E-field is not zero

Distribution function: $f_c\left(\vec{k} + \frac{e \tau}{\hbar} \vec{E}\right)$

Current density can be obtained by the familiar expression:

$$\vec{J} = -e \times 2 \times 2 \times \int_{\text{near } \vec{k}_0} \frac{d^2 \vec{k}}{(2\pi)^2} f\left(\vec{k} + \frac{e \tau}{\hbar} \vec{E}\right) \vec{v}(\vec{k})$$

2 pockets or valleys 2 spins

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